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List of Publications by Year
in descending order

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96 papers	2,252 citations	218677 26 h-index	243625 44 g-index
96 all docs	96 docs citations	96 times ranked	1000 citing authors

#	Article	IF	Citations
1	Transfer of graphene thin film obtained by PECVD method to Au/p-Si rectifier junction as interfacial layer and analysis of its barrier characteristics depending on sample temperature. Journal of Materials Science: Materials in Electronics, 2022, 33, 14627-14643.	2.2	3
2	Effects of aging on the electrical properties of Au/n-Si/Ti, Cu/n-Si/Ti and AuCu/n-Si/Ti Schottky diodes. Materials Today: Proceedings, 2021, 46, 6954-6959.	1.8	1
3	The temperature dependence of current-voltage characteristics of CuAuAg/n-Si/Ti Schottky diode. Materials Today: Proceedings, 2021, 46, 6924-6928.	1.8	2
4	Interpretation of the Iâ€“V, Câ€“V and G/Ï‰-V characteristics of the Au/ZnS/n-GaAs/In structure depending on annealing temperature. Physica B: Condensed Matter, 2021, 611, 412801.	2.7	2
5	Role of Reduced Graphene Oxide-Gold Nanoparticle Composites on Au/Au-RGO/p-Si/Al Structure Depending on Sample Temperature. Journal of Electronic Materials, 2021, 50, 4752-4761.	2.2	8
6	Annealing effect on I-V and C-V characteristics of Al/n-InP Schottky diodes at low temperatures. Materials Today: Proceedings, 2021, 46, 6979-6985.	1.8	5
7	Optimizing quality of lead-free perovskite thin film with anti-solvent engineering and co-doping SnBr2/SnF2; its solar cell performance. Optical Materials, 2020, 110, 110524.	3.6	16
8	Effects of surface passivation on capacitance-voltage and conductance-voltage characteristics of Al/p-type Si/Al and Al/V2O5/p-type Si/Al diodes. Journal of Physics and Chemistry of Solids, 2020, 146, 109564.	4.0	10
9	A comparative study on theoretical and experimental methods using basic electrical parameters of Au/CNTs/InP/Auâ€“Ge diodes. Journal of Alloys and Compounds, 2020, 824, 153899.	5.5	5
10	Analysis of thermal annealing effects of Au-Cu/n-GaAs/In and Ag-Cu/n- GaAs/In Schottky diodes with different ratios Au-Cu and Ag-Cu alloys. Materials Today: Proceedings, 2019, 18, 1918-1926.	1.8	2
11	The protection from the effects of gamma rays of metal-semiconductor diodes by means of ZnO thin interface layer. Radiation Physics and Chemistry, 2019, 165, 108416.	2.8	9
12	The electrical current characteristics of thermally annealed Co/anodic oxide layer/n-GaAs sandwich structures. International Journal of Modern Physics B, 2019, 33, 1950232.	2.0	3
13	Effect of electron radiation on electrical parameters of Zn/n-Si/Auâ€“Sb and Zn/ZnO/n-Si/Auâ€“Sb diodes. Journal of Radioanalytical and Nuclear Chemistry, 2019, 319, 667-678.	1.5	11
14	Barrier Height Modification of n-InP Using a Silver Nanoparticles Loaded Graphene Oxide as an Interlayer in a Wide Temperature Range. Journal of Electronic Materials, 2019, 48, 3169-3182.	2.2	15
15	Effects of Au-Ag and Au-Cu alloy ratios on the temperature dependent current-voltage characteristics of Au-Ag/n-GaAs/In and Au-Cu/n-GaAs/In Schottky diodes. Materials Today: Proceedings, 2019, 18, 1936-1945.	1.8	2
16	The effects of gamma irradiation on electrical characteristics of Zn/ZnO/n-Si/Au-Sb structure. AIP Conference Proceedings, 2018, , .	0.4	1
17	Influence of anodic passivation on electrical characteristics of Al/p-Si/Al and Al/V2O5/p-Si/Al diodes. Journal of Materials Science: Materials in Electronics, 2017, 28, 7582-7592.	2.2	8
18	Nanorods/nanostructral vanadium oxide prepared by spray pyrolysis. AIP Conference Proceedings, 2017, , .	0.4	0

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19	The stability of electrical characteristics of Ti/n-Si/Ag , Ti/n-Si/Cu and Ti/n-Si/AgCu diodes prepared under the same conditions with respect to increasing aging time. Materials Science in Semiconductor Processing, 2017, 68, 186-192.	4.0	7
20	Analysis of aging time dependent electrical characteristics of AuCu/n-Si/Ti Schottky type diode. AIP Conference Proceedings, 2017, , .	0.4	0
21	Characterization of deposited CdS thin films by Spray Pyrolysis method and used in Cd/CdS/p-Si/Al structure. AIP Conference Proceedings, 2017, , .	0.4	0
22	Effects Of the Î³- radiation on the electrical characteristics of the Au/n-Si/Au-Sb Schottky diode. Journal of Physics: Conference Series, 2016, 707, 012018.	0.4	4
23	Investigation of the Electrical Characteristics of Al/p-Si/Al Schottky Diode. Journal of Physics: Conference Series, 2016, 707, 012013.	0.4	7
24	Effects of ageing on the electrical characteristics of Zn/ZnS/n-GaAs/In structure. Journal of Physics: Conference Series, 2016, 707, 012016.	0.4	0
25	Time-dependent of characteristics of Cu/CuS/n-GaAs/In structure produced by SILAR method. Materials Research Bulletin, 2016, 81, 55-62.	5.2	9
26	The Effects of Growth Parameters on Electrical Characteristics of In2S3/n-InP Junctions with In2S3 Interfacial Layer Obtained by Chemical Spray Pyrolysis Method. Materials Today: Proceedings, 2016, 3, 1262-1270.	1.8	2
27	Temperature dependent electrical characteristics of Zn/ZnSe/n-GaAs/In structure. Journal of Physics: Conference Series, 2016, 707, 012025.	0.4	3
28	Determination of the some electronic parameters of nanostructure copper selenide and Cu/Cu3Se2/n-GaAs/In structure. Journal of Alloys and Compounds, 2015, 627, 200-205.	5.5	26
29	Temperature dependent electrical properties of Cd/CdS/n-Si/Au-Sb structures. Materials Science in Semiconductor Processing, 2015, 30, 658-664.	4.0	6
30	Temperature dependent of electrical characteristics of Au/n-GaAs/In Schottky diode with In2S3 interfacial layer obtained by using spray pyrolysis method. Journal of Alloys and Compounds, 2015, 646, 954-965.	5.5	21
31	Using different chemical methods for deposition of copper selenide thin films and comparison of their characterization. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2015, 150, 111-119.	3.9	13
32	The comparison of electrical characteristics of Au/n-InP/In and Au/In2S3/n-InP/In junctions at room temperature. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2015, 193, 61-69.	3.5	17
33	The effects of thermal annealing on the electrical characteristics of Au/nâ€“InP/In diode. Materials Science in Semiconductor Processing, 2014, 28, 121-126.	4.0	10
34	Temperature dependence of currentâ€“voltage characteristics of the Cd/CdS/n-GaAs/In sandwich structure. Journal of Physics and Chemistry of Solids, 2013, 74, 370-376.	4.0	8
35	Some electrical and structural properties of Cd/CdS/nâ€“Si/Auâ€“Sb sandwich structure. Superlattices and Microstructures, 2012, 52, 416-429.	3.1	10
36	Effect of temperature on the capacitanceâ€“frequency and conductanceâ€“voltage characteristics of polyaniline/p-Si/Al MIS device at high frequencies. Microelectronics Reliability, 2012, 52, 1362-1366.	1.7	29

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37	Conductance and series resistance measurements of polyaniline/p-Si and polypyrrole/InP junction devices. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 46, 38-42.	2.7	4
38	Influence of film thickness on structural and optical properties of ZnS thin films obtained by SILAR method and analysis of Zn/ZnS/nâ€GaAs/In sandwich structure. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 687-693.	1.8	18
39	Deposition and Characterization of CdS, CuS and ZnS Thin Films Deposited by SILAR Method. Acta Physica Polonica A, 2012, 121, 33-35.	0.5	27
40	Temperature Dependent Electrical Characteristics Of Cuâ•CuSâ•n-Siâ•Au-Sb Structure Deposited By SILAR Method. AIP Conference Proceedings, 2011, , .	0.4	1
41	Temperature dependent currentâ€“voltage characteristics of the Zn/ZnO/n-Si/Auâ€“Sb structure with ZnO interface layer grown on n-Si substrate by SILAR method. Microelectronic Engineering, 2011, 88, 3075-3079.	2.4	22
42	Laterally inhomogeneous barrier analysis of identically prepared Cd/CdS/n-Si/Auâ€“Sb structures by SILAR method. Microelectronics Reliability, 2011, 51, 2179-2184.	1.7	6
43	Effects of ageing on the electrical characteristics of Cd/CdS/n-Si/Auâ€“Sb structure deposited by SILAR method. Journal of Physics and Chemistry of Solids, 2011, 72, 1506-1514.	4.0	17
44	ZnS thin film and Zn/ZnS/n-Si/Au-Sb sandwich structure grown with SILAR method and defining the characteristic parameters. Materials Science in Semiconductor Processing, 2011, 14, 28-36.	4.0	21
45	Temperature dependent currentâ€“voltage characteristics of the Cd/CdO/nâ€“Si/Auâ€“Sb structure. Current Applied Physics, 2010, 10, 513-520.	2.4	29
46	Analysis of the electrical characteristics of Zn/ZnSe/n-Si/Auâ€“Sb structure fabricated using SILAR method as a function of temperature. Journal of Alloys and Compounds, 2010, 506, 388-394.	5.5	30
47	Temperature-dependent currentâ€“voltage and capacitanceâ€“voltage characteristics of the Ag/n-InP/In Schottky diodes. Journal of Materials Science: Materials in Electronics, 2009, 20, 105-112.	2.2	31
48	Series resistance determination of Au/Polypyrrole/p-Si/Al structure by currentâ€“voltage measurements at low temperatures. Materials Science and Engineering C, 2009, 29, 1486-1490.	7.3	57
49	Temperature-dependent currentâ€“voltage characteristics of the Au/n-InP diodes with inhomogeneous Schottky barrier height. Physica B: Condensed Matter, 2009, 404, 1558-1562.	2.7	49
50	Effects of thermal annealing on electrical characteristics of Cd/CdS/n-Si/Auâ€“Sb sandwich structure. Journal of Alloys and Compounds, 2009, 484, 570-574.	5.5	25
51	Some electrical properties of polyaniline/p-Si/Al structure at 300K and 77K temperatures. Microelectronic Engineering, 2008, 85, 278-283.	2.4	97
52	Calculation from the currentâ€“voltage and capacitanceâ€“voltage measurements of characteristics parameters of Cd/CdS/n-Si/Au-Sb structure with CdS interface layer grown on n-Si substrate by SILAR method. Microelectronic Engineering, 2008, 85, 1831-1835.	2.4	3
53	Effective atomic numbers of polypyrrole via transmission method in the energy range 15.74â€“40.93keV. Annals of Nuclear Energy, 2008, 35, 432-437.	1.8	17
54	Reverse bias capacitanceâ€“voltage characteristics of Al/polyaniline/p-Si/Al structure as a function of temperature. Journal of Non-Crystalline Solids, 2008, 354, 4991-4995.	3.1	18

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55	Determination of the lateral barrier height of inhomogeneous Au/n-type InP/In Schottky barrier diodes. Semiconductor Science and Technology, 2007, 22, 851-854.	2.0	31
56	A critical look at quantum diffusion and some of its interesting aspects. European Physical Journal B, 2007, 59, 69-73.	1.5	1
57	Electrical properties of polypyrrole/p-InP structure. Journal of Polymer Science, Part B: Polymer Physics, 2006, 44, 1572-1579.	2.1	8
58	Intrinsic Magnetic Flux of the Electron's Orbital and Spin Motion. International Journal of Theoretical Physics, 2006, 45, 1132-1151.	1.2	10
59	Aging effects on the interface state density obtained from currentâ€“voltage and capacitanceâ€“frequency characteristics of polypyrrole/p-Si/Al structure. Journal of Applied Polymer Science, 2006, 101, 2313-2319.	2.6	11
60	The temperature dependence of currentâ€“voltage characteristics of the Au/Polypyrrole/p-Si/Al heterojunctions. Journal of Physics Condensed Matter, 2006, 18, 2665-2676.	1.8	44
61	The effects of the temperature on the some parameters obtained from currentâ€“voltage and capacitanceâ€“voltage characteristics of polypyrrole/n-Si structure. Polymer, 2005, 46, 563-568.	3.8	77
62	Characterization of capacitanceâ€“frequency features of Sn/polypyrrole/n-Si structure as a function of temperature. Polymer, 2005, 46, 6148-6153.	3.8	35
63	Currentâ€“voltage and capacitanceâ€“voltage characteristics of polypyrrole/p-InP structure. Vacuum, 2005, 77, 269-274.	3.5	90
64	On the barrier inhomogeneities of polyaniline/p-Si/Al structure at low temperature. Applied Surface Science, 2005, 250, 43-49.	6.1	98
65	On the some electrical properties of the non-ideal PPy/p-Si/Al structure. Polymer, 2005, 46, 10982-10988.	3.8	60
66	Determination of the Characteristic Parameters of Polyaniline/p-type Si/Al Structures from Current-Voltage Measurements. International Journal of Polymeric Materials and Polymeric Biomaterials, 2005, 54, 805-813.	3.4	11
67	The effects of the temperature on currentâ€“voltage characteristics of Sn/polypyrrole/n-Si structures. Synthetic Metals, 2005, 150, 15-20.	3.9	28
68	Experimental determination of the laterally homogeneous barrier height of Au/n-Si Schottky barrier diodes. Physica B: Condensed Matter, 2004, 348, 397-403.	2.7	44
69	The effects of the time-dependent on the characteristic parameters of polypyrrole/p-type Si/Al diode. Polymer, 2004, 45, 7335-7340.	3.8	34
70	The effects of the ageing on the characteristic parameters of polyaniline/p-type Si/Al structure. Applied Surface Science, 2004, 230, 404-410.	6.1	24
71	Conductance and capacitance-frequency characteristics of polypyrrole/p-type silicon structures. Journal of Polymer Science, Part B: Polymer Physics, 2003, 41, 1334-1338.	2.1	18
72	The absence of an ideal two dimensionality in QHE. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1493-1496.	0.8	0

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73	Magnetic Superlattice: Localized Magnetostatic Waves and Magnetic Polaritons. Modern Physics Letters B, 2003, 17, 829-839.	1.9	0
74	CALCULATION OF THE FLUX ASSOCIATED WITH THE ELECTRON'S SPIN ON THE BASIS OF THE MAGNETIC TOP MODEL. International Journal of Modern Physics B, 2002, 16, 607-614.	2.0	15
75	The Absence of Decimalg-Factor in QHE. Physica Status Solidi (B): Basic Research, 2002, 230, 133-142.	1.5	4
76	High-barrier height Sn/p-Si schottky diodes with interfacial layer by anodization process. Applied Surface Science, 2001, 172, 1-7.	6.1	42
77	Currentâ€“voltage and capacitanceâ€“voltage characteristics of metallic polymer/InSe(:Er) Schottky contacts. Microelectronic Engineering, 2000, 51-52, 689-693.	2.4	14
78	On the Forward Bias Excess Capacitance at Intimate and MIS Schottky Barrier Diodes with Perfect or Imperfect Ohmic Back Contact. Physica Scripta, 2000, 61, 209-212.	2.5	58
79	Cr/- and Fe/n-GaAs Schottky diodes: the stable current-voltage characteristic produced by high-temperature annealing. Semiconductor Science and Technology, 1999, 14, 114-117.	2.0	7
80	On The Experimental Forward Capacitance-Voltage Characteristics of Schottky Barrier Diodes. Journal for Manufacturing Science and Production, 1999, 2, 145-150.	0.1	0
81	The effects of the time-dependent and exposure time to air on Au/epilayer n-Si Schottky diodes. EPJ Applied Physics, 1999, 6, 89-94.	0.7	24
82	Thermal treatment of the MIS and intimate Ni/n-LEC GaAs Schottky barrier diodes. Applied Surface Science, 1998, 135, 350-356.	6.1	17
83	Thermal stability of Cr-Ni-Co alloy Schottky contacts on MBE -GaAs. Semiconductor Science and Technology, 1998, 13, 776-780.	2.0	6
84	The Effect of Thermal Anealing on the Series Resistance of Nearly Ideal and Ideal Ti/n-GaAs Schottky Diodes. Physica Scripta, 1998, 58, 636-639.	2.5	5
85	Effect of thermal annealing in nitrogen on theI - VandC - Vcharacteristics of Cr - Ni - Co alloy/LEC n-GaAs Schottky diodes. Semiconductor Science and Technology, 1997, 12, 1028-1031.	2.0	32
86	Influences of thermal annealing, the electrolyte pH, and current density on the interface state density distribution of anodic MOS structures. Applied Physics A: Materials Science and Processing, 1997, 65, 33-37.	2.3	14
87	Characteristics of metallic polymer and Au Schottky contacts on cleaved surfaces of InSe(:Er). Solid-State Electronics, 1997, 41, 924-926.	1.4	9
88	Effect of series resistance on the forward current-voltage characteristics of Schottky diodes in the presence of interfacial layer. Solid-State Electronics, 1996, 39, 83-87.	1.4	89
89	High barrier metallic polymer/p-type silicon Schottky diodes. Solid-State Electronics, 1996, 39, 677-680.	1.4	61
90	The bias-dependence change of barrier height of Schottky diodes under forward bias by including the series resistance effect. Physica Scripta, 1996, 53, 118-122.	2.5	93

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91	Series resistance calculation for the Metal-Insulator-Semiconductor Schottky barrier diodes. Applied Physics A: Materials Science and Processing, 1996, 62, 269-273.	2.3	7
92	Interpreting the nonideal reverse bias C-V characteristics and importance of the dependence of Schottky barrier height on applied voltage. Physica B: Condensed Matter, 1995, 205, 41-50.	2.7	150
93	Barrier height enhancement by annealing Crî—¸Niî—¸Co alloy Schottky contacts on LEC GaAs. Solid-State Electronics, 1992, 35, 1423-1426.	1.4	11
94	Parameter extraction from non-ideal Câ^'V characteristics of a Schottky diode with and without interfacial layer. Solid-State Electronics, 1992, 35, 835-841.	1.4	148
95	Determination of the density of Si-metal interface states and excess capacitance caused by them. Physica B: Condensed Matter, 1992, 179, 285-294.	2.7	75
96	Nanostructures and Properties of Vanadium Oxide Thin Film Prepared by Spray Pyrolysis Method. Materials Science Forum, 0, 890, 287-290.	0.3	0